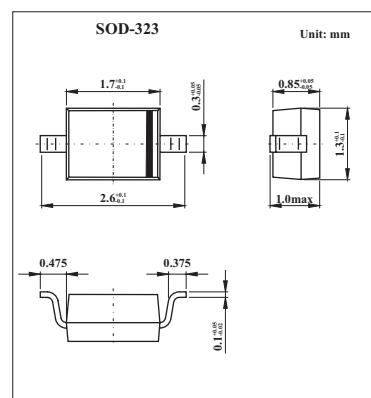


Silicon Schottky Diode

BAT62-03W

■ Features

- Low Barrier diode for detectors up to GHz frequencies

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	40	V
Forward current	I_F	40	mA
Junction current	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$
Total power dissipation	P_{tot}	100	mW
Junction ambient ⁽¹⁾	R_{thJA}	≤ 650	K/W
Junction-soldering point	R_{thJS}	≤ 810	K/W

Note:

1. Package mounted on an epoxy pcb 15 mm × 16.7mm × 0.7 mm

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Breakdown current	I_R	$V_R = 40\text{ V}, T_A = 25^\circ\text{C}$			10	μA
Forward voltage	V_F	$I_F = 2\text{ mA}$		0.58	1	V
Diode capacitance	C_T	$V_R = 0; f = 1\text{ MHz}$		0.35	0.6	pF
Case capacitance	C_C	$f = 1\text{ MHz}$		0.1		pF
Differential forward resistance	R_O	$V_R = , f = 10\text{ kHz}$		225		k Ω
Series inductance chip to ground	L_S			2		nH

■ Marking

Marking	L
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